



**Absolute Maximum Ratings: NPN, BC847B Type (Q<sub>1</sub>)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	45	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Collector Current	I <sub>C</sub>	100	mA
Peak Collector Current	I <sub>CM</sub>	200	mA
Peak Emitter Current	I <sub>EM</sub>	200	mA

**Absolute Maximum Ratings: PNP, BC857B Type (Q<sub>2</sub>)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CB0</sub>	-50	V
Collector-Emitter Voltage	V <sub>CEO</sub>	-45	V
Emitter-Base Voltage	V <sub>EBO</sub>	-6	V
Collector Current	I <sub>C</sub>	-100	mA
Peak Collector Current	I <sub>CM</sub>	-200	mA
Peak Emitter Current	I <sub>EM</sub>	-200	mA

**Thermal Characteristics – Total Device** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6) Total Device	P <sub>D</sub>	200	mW
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	625	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150	°C

Note: 6. For a device mounted on minimum recommended pad layout with 1oz copper that is on a single-sided 1.6mm FR-4 PCB; the device is measured under still air conditions whilst operating in a steady-state.

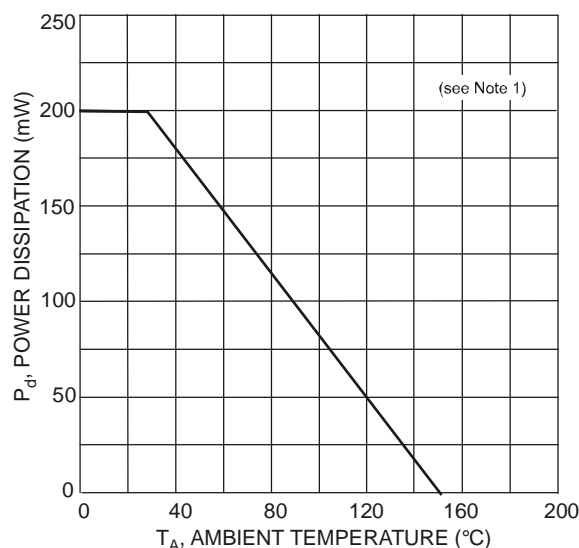
**Thermal Characteristics – Total Device**


Fig. 1, Power Derating Curve (Total Device)

**Electrical Characteristics: NPN, BC847B Type (Q<sub>1</sub>)** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic (Note 7)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CE0</sub>	50	—	—	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	45	—	—	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	—	—	V	I <sub>E</sub> = 100μA
DC Current Gain	h <sub>FE</sub>	200	290	450	—	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	90 200	250 600	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	700 900	—	mV	I <sub>C</sub> = 10mA, I <sub>B</sub> = 0.5mA I <sub>C</sub> = 100mA, I <sub>B</sub> = 5.0mA
Base-Emitter Voltage	V <sub>BE(ON)</sub>	580 —	660 —	700 720	mV	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 2.0mA V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA
Collector-Cutoff Current	I <sub>CBO</sub>	—	—	15 5.0	nA μA	V <sub>CB</sub> = 30V V <sub>CB</sub> = 30V, T <sub>A</sub> = +150°C
Gain Bandwidth Product	f <sub>T</sub>	100	300	—	MHz	V <sub>CE</sub> = 5.0V, I <sub>C</sub> = 10mA, f = 100MHz
Collector-Base Capacitance	C <sub>CB0</sub>	—	3.5	6.0	pF	V <sub>CB</sub> = 10V, f = 1.0MHz
Noise Figure	NF	—	2.0	10	dB	V <sub>CE</sub> = 5V, I <sub>C</sub> = 200μA, R <sub>g</sub> = 2.0kΩ, f = 1.0kHz, Δf = 200Hz

Note: 7. Short duration pulse test used to minimize self-heating effect.

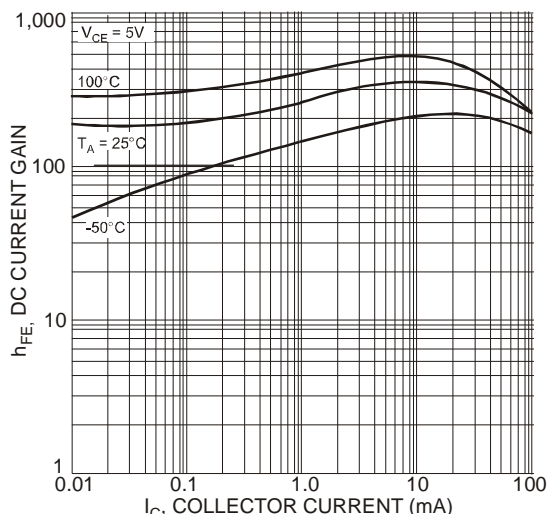


Figure 2. Typical DC Current Gain vs. Collector Current (BC847B Type)

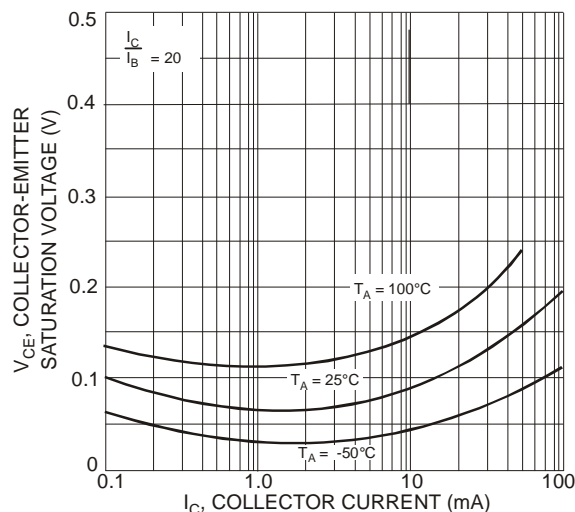


Figure 3. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC847B Type)

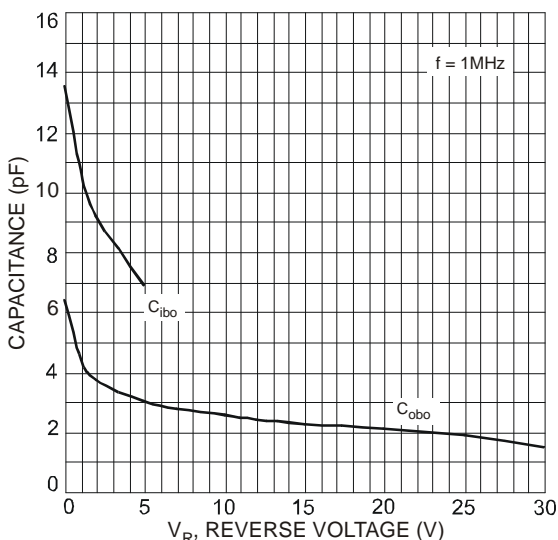


Figure 4. Typical Capacitance Characteristics (BC847B Type)

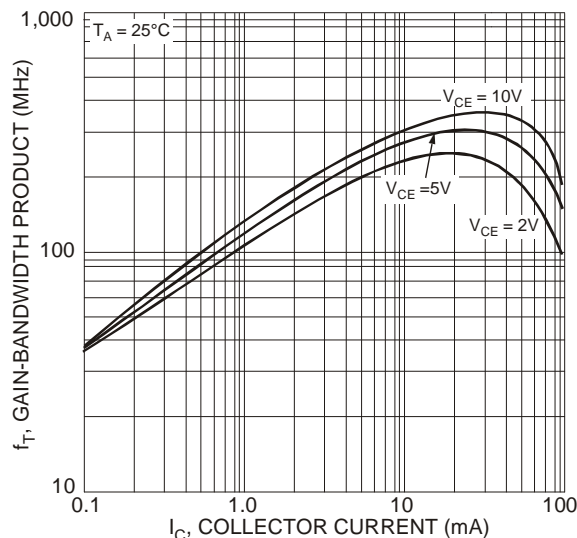


Figure 5. Typical Gain-Bandwidth Product vs. Collector Current (BC847B Type)

**Electrical Characteristics: PNP, BC857B Type (Q<sub>2</sub>)** (@T<sub>A</sub> = +25°C unless otherwise specified.)

Characteristic (Note 8)	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	-50	—	—	V	I <sub>C</sub> = -100μA
Collector-Emitter Breakdown Voltage	BV <sub>CEO</sub>	-45	—	—	V	I <sub>C</sub> = -10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	-6	—	—	V	I <sub>E</sub> = -100μA
DC Current Gain	h <sub>FE</sub>	220	290	475	—	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>	—	-75 -250	-300 -650	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>	—	-700 -850	— -950	mV	I <sub>C</sub> = -10mA, I <sub>B</sub> = -0.5mA I <sub>C</sub> = -100mA, I <sub>B</sub> = -5.0mA
Base-Emitter Voltage	V <sub>BE(ON)</sub>	-600 —	-650 —	-750 -820	mV	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -2.0mA V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA
Collector-Cutoff Current	I <sub>CBO</sub>	— —	— —	-15 -4.0	nA μA	V <sub>CB</sub> = -30V V <sub>CB</sub> = -30V, T <sub>A</sub> = +150°C
Gain Bandwidth Product	f <sub>T</sub>	100	200	—	MHz	V <sub>CE</sub> = -5.0V, I <sub>C</sub> = -10mA, f = 100MHz
Collector-Base Capacitance	C <sub>CBO</sub>	—	3	4.5	pF	V <sub>CB</sub> = -10V, f = 1.0MHz
Noise Figure	NF	—	—	10	dB	V <sub>CE</sub> = -5V, I <sub>C</sub> = -200μA, R <sub>g</sub> = 2.0kΩ, f = 1.0kHz, Δf = 200Hz

Note: 8. Short duration pulse test used to minimize self-heating effect.

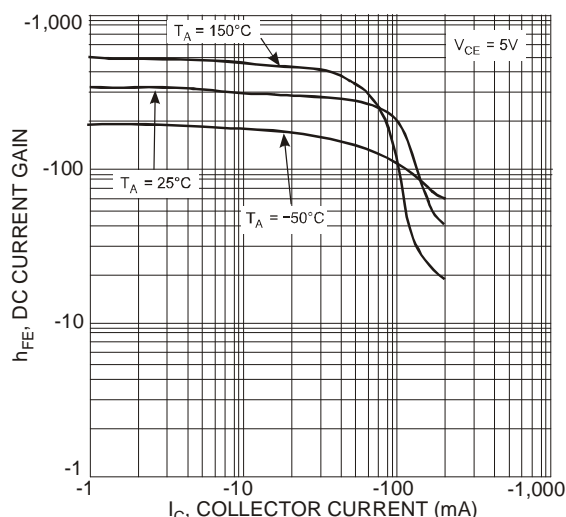


Figure 6. Typical DC Current Gain vs. Collector Current (BC857B Type)

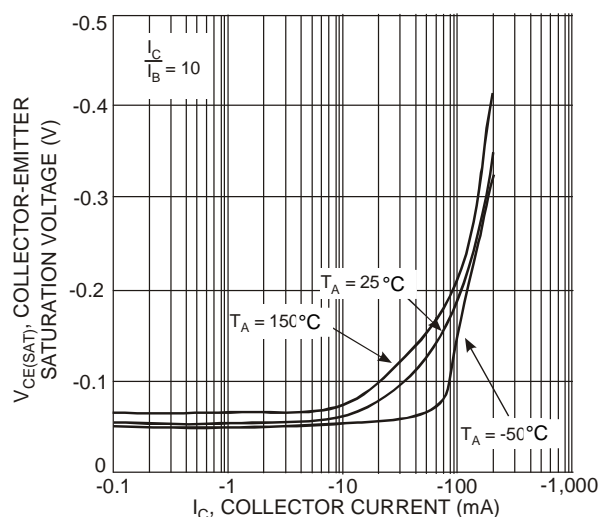


Figure 7. Typical Collector-Emitter Saturation Voltage vs. Collector Current (BC857B Type)

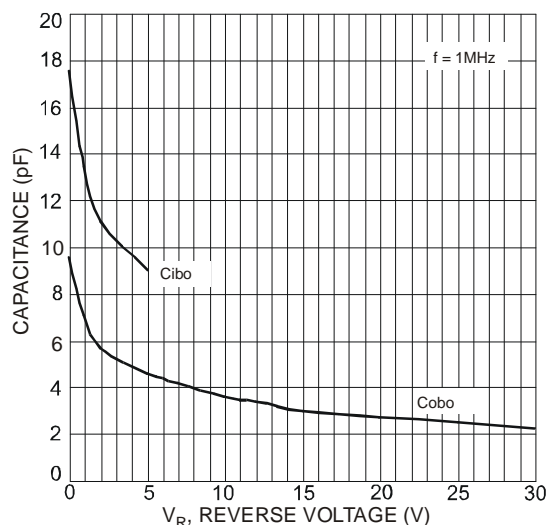


Figure 8. Typical Capacitance Characteristics (BC857B Type)

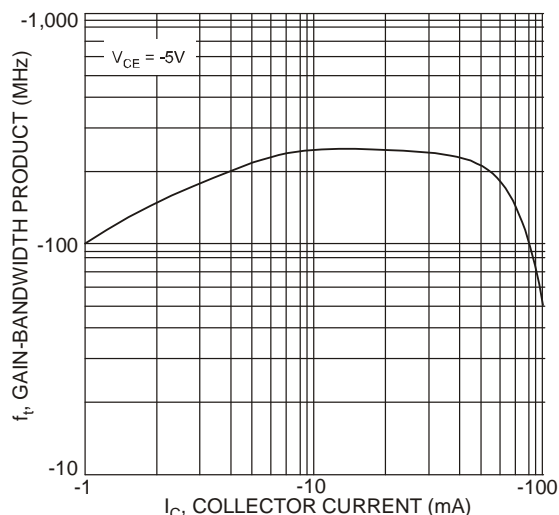
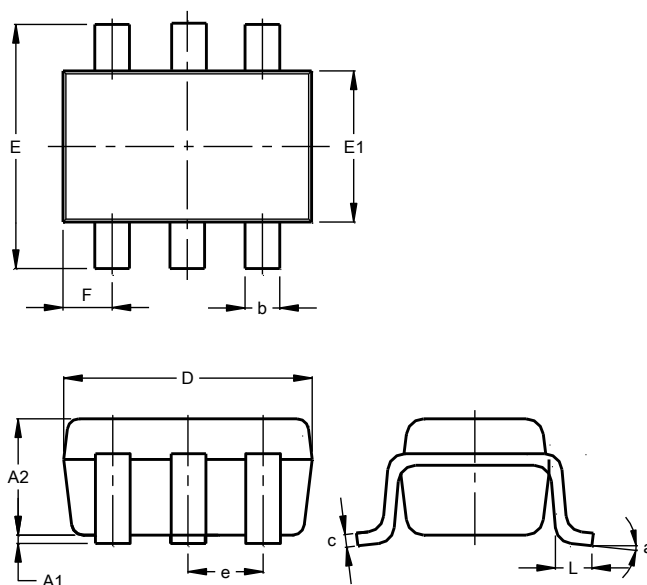


Figure 9. Typical Gain-Bandwidth Product vs. Collector Current (BC857B Type)

## Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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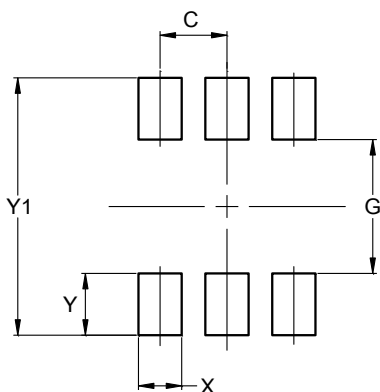


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Dim	Min	Max	Typ
A1	0.00	0.10	0.05
A2	0.90	1.00	1.00
b	0.10	0.30	0.25
c	0.10	0.22	0.11
D	1.80	2.20	2.15
E	2.00	2.20	2.10
E1	1.15	1.35	1.30
e	0.650 BSC		
F	0.40	0.45	0.425
L	0.25	0.40	0.30
a	0°	8°	--
All Dimensions in mm			

## Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

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Dimensions	Value (in mm)
C	0.650
G	1.300
X	0.420
Y	0.600
Y1	2.500

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